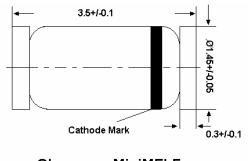
LL103A...LL103C

SILICON SCHOTTKY BARRIER DIODES

for general purpose applications

The LL103A, B, C is a metal on Silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications. Other uses are for click suppression, efficient full wave bridges in telephone subsets, and as blocking diodes in rechargeable low voltage battery systems.



Glass case MiniMELF Dimensions in mm

This diode is also available in DO-35 case with type designation SD103A, B, C.

Absolute Maximum Ratings (T_a = 25°C)

		Symbol	Value	Unit
Peak Reverse Voltage	LL103A	V _{RRM}	40	V
	LL103B	V _{RRM}	30	V
	LL103C	V _{RRM}	20	V
Power Dissipation (Infinite Heatsink)				
Tc = 3/8 from body		P _{tot}	400 ¹⁾	mW
Derates at 4 mW/°C to 0 at 125 °C				
Single Cycle Surge 60Hz sinewave		I _{FSM}	15	А
Junction Temperature		Tj	125	°C
Storage Temperature Range		Ts	-55 to +175	°C
¹⁾ Valid provided that electrodes are kept at a	ambient temperature			







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LL103A...LL103C

Characteristics at $T_{amb} = 25^{\circ}C$

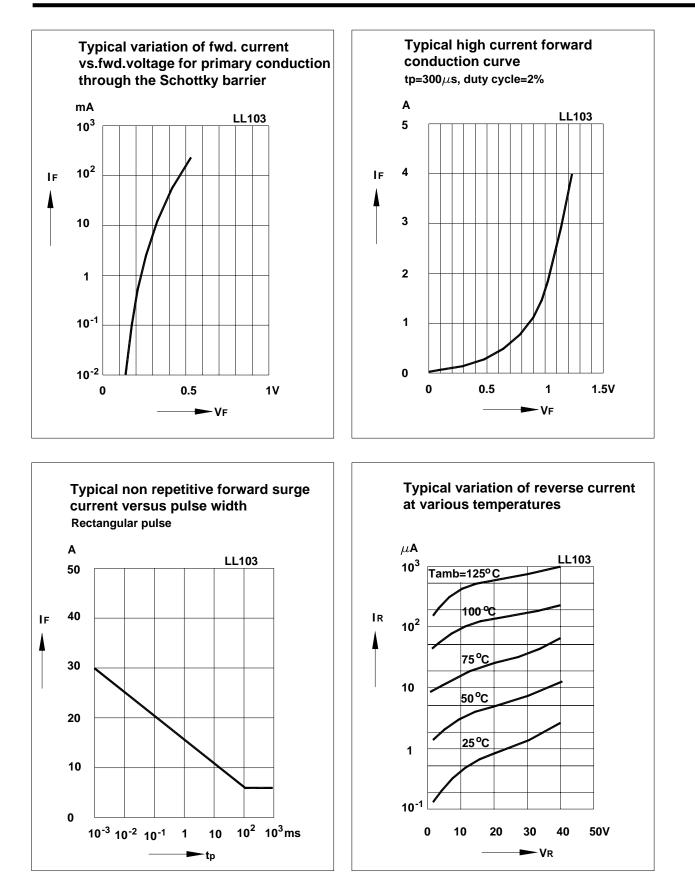
		Symbol	Min.	Тур.	Max.	Unit
Forward Voltage						
at I _F = 20mA		V_{F}	-	-	0.37	V
at I _F = 200mA		V _F	-	-	0.6	V
Leakage Current						
at $V_R = 30V$	LL103A	I _R	-	-	5	uA
at $V_R = 20V$	LL103B	I _R	-	-	5	uA
at V _R =10V	LL103C	I _R	-	-	5	uA
Junction Capacitance at $V_R = 0V$, f = 1MHz		C _{tot}	-	50	-	pF
Reverse Recovery Time at $I_F = I_R = 5$ mA to 200 mA , recover to	0.1 l _R	t _{rr}	-	10	-	ns







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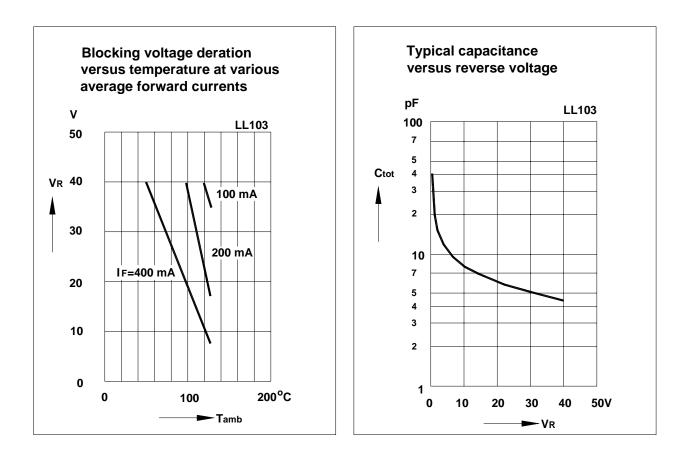








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